

## SWITCHING

## P-CHANNEL POWER MOS FET

### DESCRIPTION

The 2SJ673 is P-channel MOS Field Effect Transistor designed for high current switching applications.

### ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ673	Isolated TO-220 (MP-45F)

### FEATURES

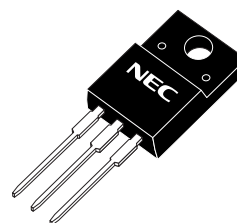
- Super low on-state resistance

$R_{DS(on)1} = 20 \text{ m}\Omega \text{ MAX. (} V_{GS} = -10 \text{ V, } I_D = -18 \text{ A)}$

$R_{DS(on)2} = 31 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -18 \text{ A)}$

- Low  $C_{iss}$ :  $C_{iss} = 4600 \text{ pF TYP.}$
- Built-in gate protection diode

(Isolated TO-220)



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Drain to Source Voltage ( $V_{GS} = 0 \text{ V}$ )	$V_{DSS}$	-60	V
Gate to Source Voltage ( $V_{DS} = 0 \text{ V}$ )	$V_{GSS}$	$\pm 20$	V
Drain Current (DC) ( $T_C = 25^\circ\text{C}$ )	$I_{D(DC)}$	$\pm 36$	A
Drain Current (pulse) <sup>Note1</sup>	$I_{D(pulse)}$	$\pm 144$	A
Total Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_{T1}$	32	W
Total Power Dissipation ( $T_A = 25^\circ\text{C}$ )	$P_{T2}$	2.0	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Single Avalanche Current <sup>Note2</sup>	$I_{AS}$	-36	A
Single Avalanche Energy <sup>Note2</sup>	$E_{AS}$	130	mJ

**Notes 1.**  $PW \leq 10 \text{ }\mu\text{s}$ , Duty Cycle  $\leq 1\%$

**2.** Starting  $T_{ch} = 25^\circ\text{C}$ ,  $V_{DD} = -30 \text{ V}$ ,  $R_G = 25 \text{ }\Omega$ ,  $V_{GS} = 20 \rightarrow 0 \text{ V}$

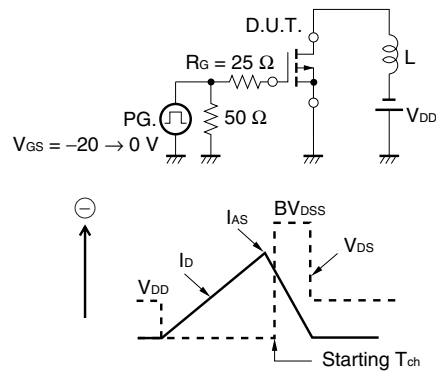
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# ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

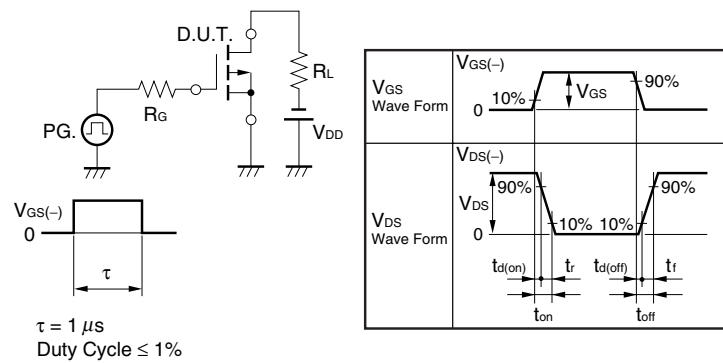
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V			-10	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±10	μA
Gate Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-1.5	-2.0	-2.5	V
Forward Transfer Admittance <b>Note</b>	y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -18 A	22			S
Drain to Source On-state Resistance <b>Note</b>	R <sub>DS(on)1</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -18 A		17	20	mΩ
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = -4.0 V, I <sub>D</sub> = -18 A		22	31	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V		4600		pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V		820		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1 MHz		330		pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -30 V, I <sub>D</sub> = -18 A		14		ns
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = -10 V		14		ns
Turn-off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> = 0 Ω		130		ns
Fall Time	t <sub>f</sub>			50		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = -48 V		87		nC
Gate to Source Charge	Q <sub>GS</sub>	V <sub>GS</sub> = -10 V		15		nC
Gate to Drain Charge	Q <sub>GD</sub>	I <sub>D</sub> = -36 A		22		nC
Body Diode Forward Voltage <b>Note</b>	V <sub>F(S-D)</sub>	I <sub>F</sub> = -36 A, V <sub>GS</sub> = 0 V		1.0		V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -36 A, V <sub>GS</sub> = 0 V		52		ns
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100 A/μs		84		nC

**Note** Pulsed

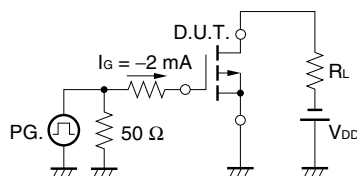
## TEST CIRCUIT 1 AVALANCHE CAPABILITY



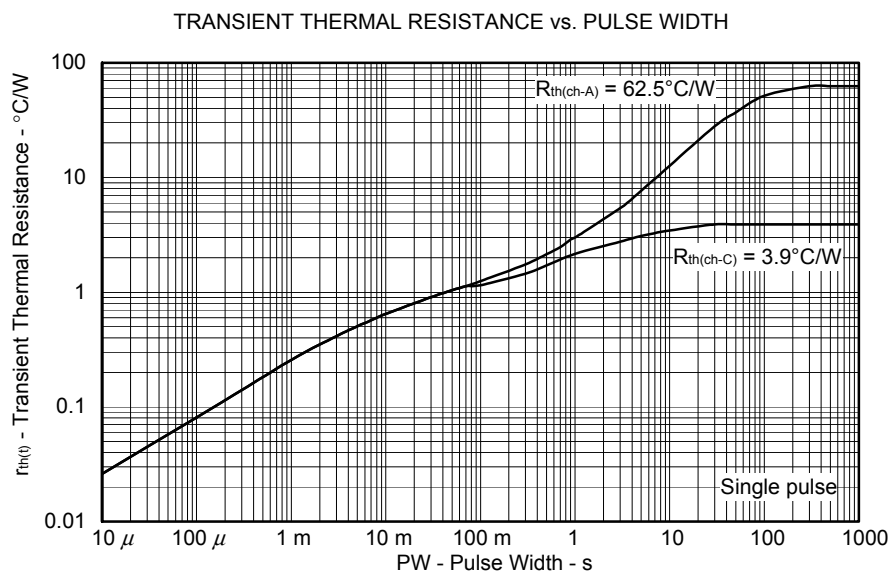
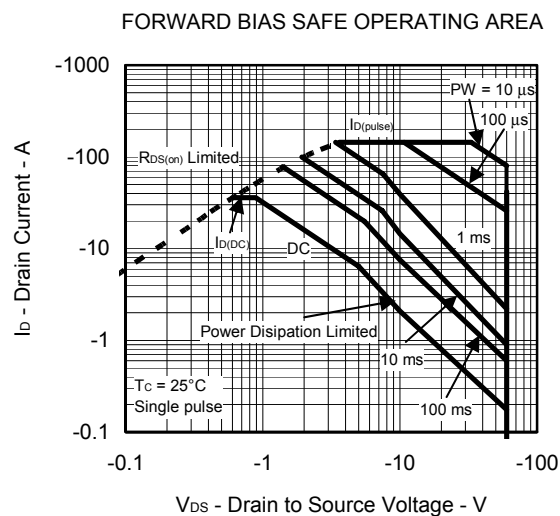
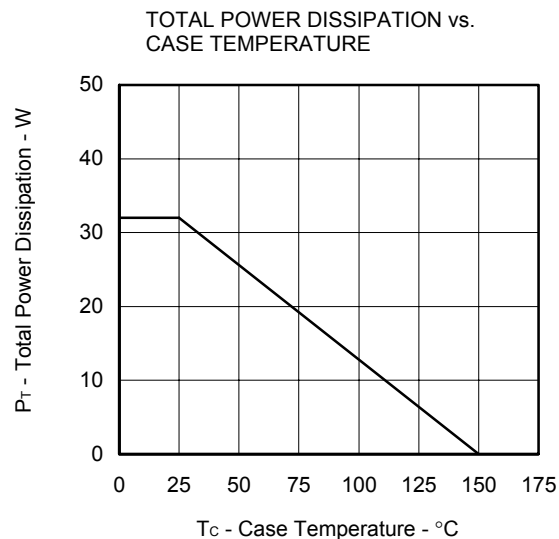
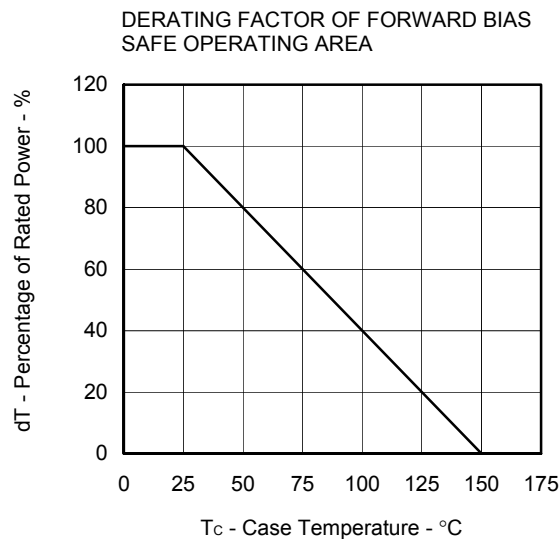
## TEST CIRCUIT 2 SWITCHING TIME



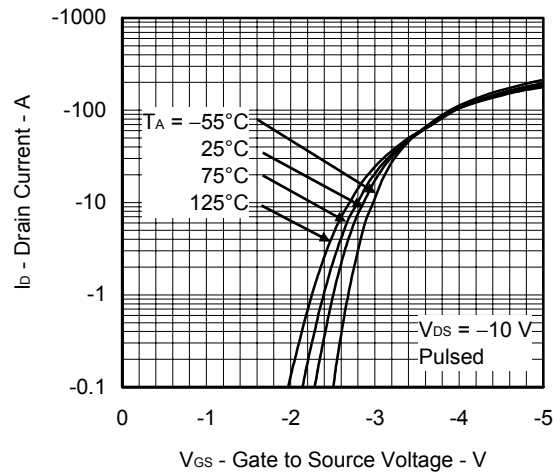
## TEST CIRCUIT 3 GATE CHARGE



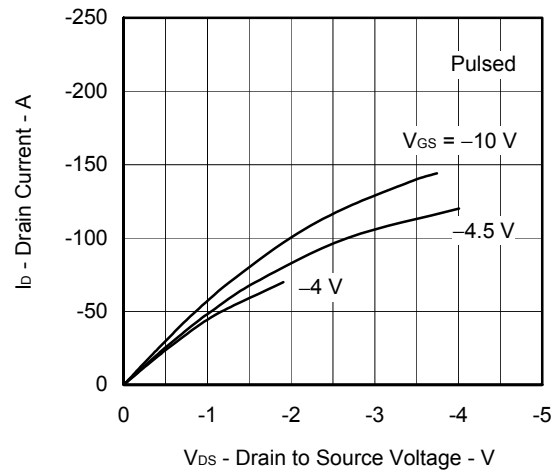
TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )



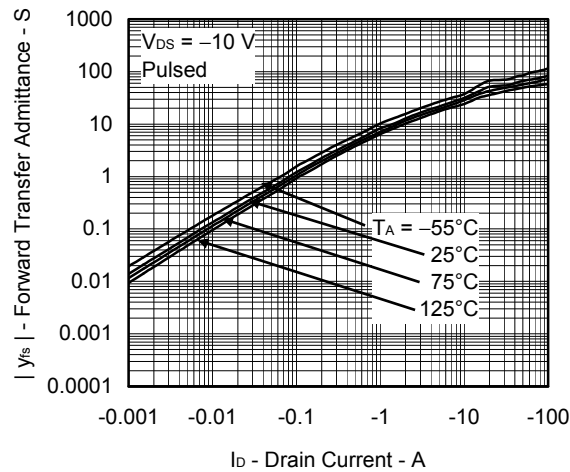
FORWARD TRANSFER CHARACTERISTICS



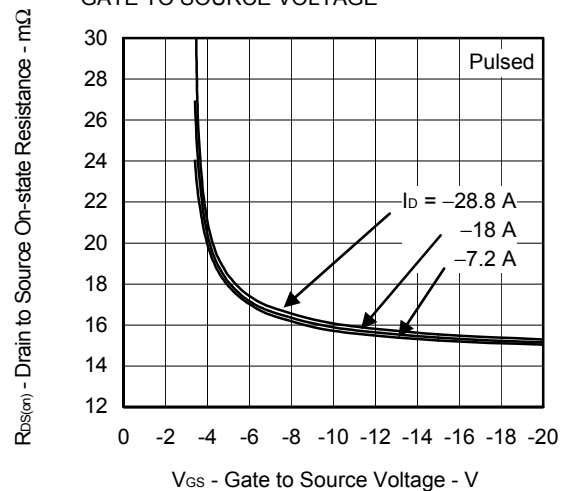
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



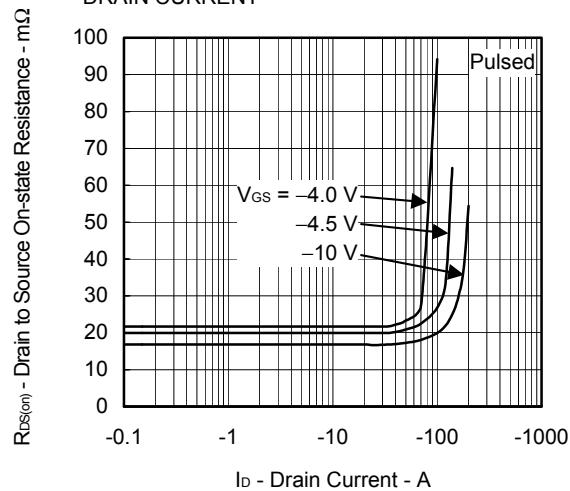
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



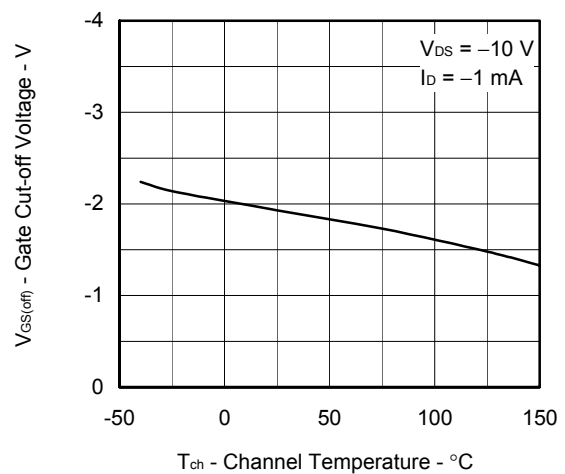
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



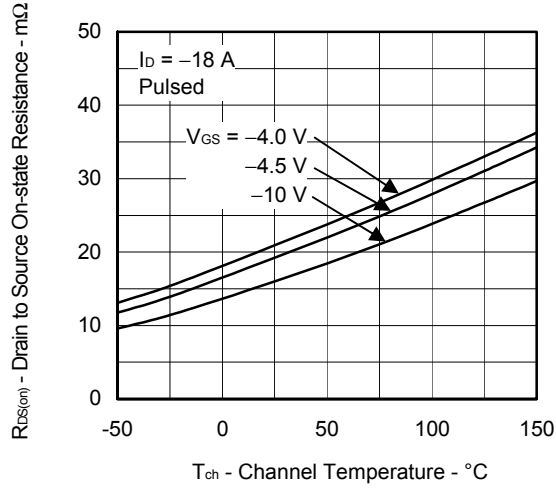
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



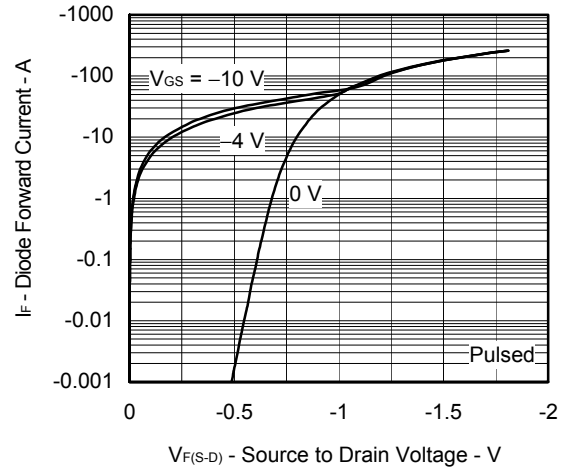
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



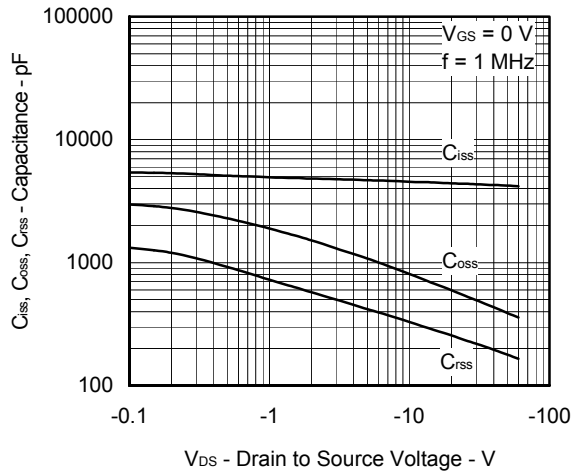
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



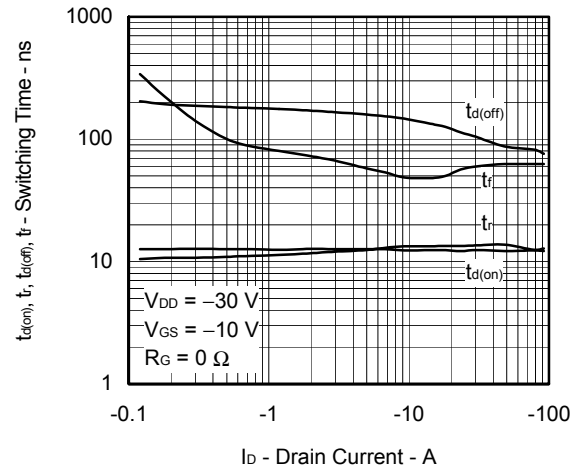
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



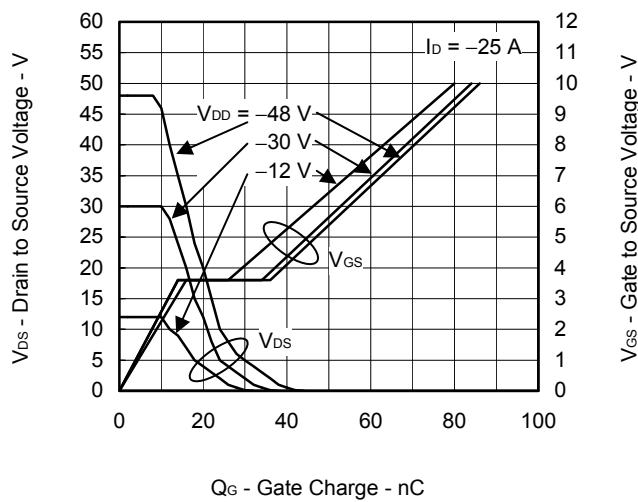
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



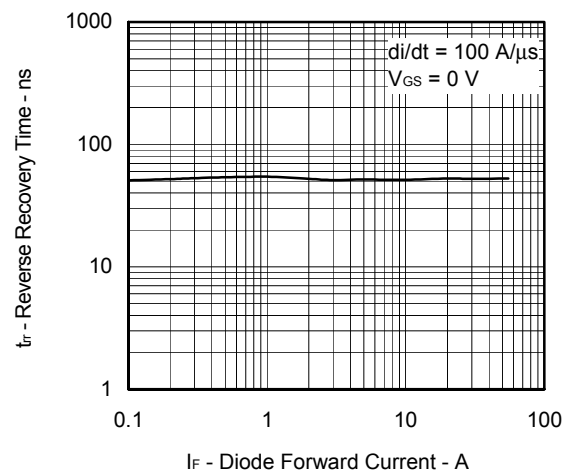
SWITCHING CHARACTERISTICS

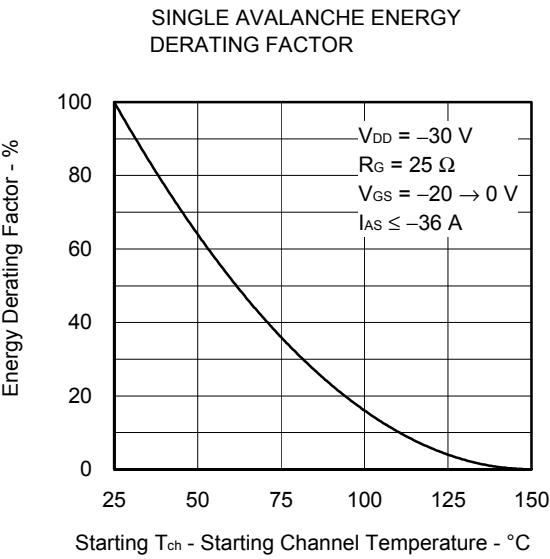
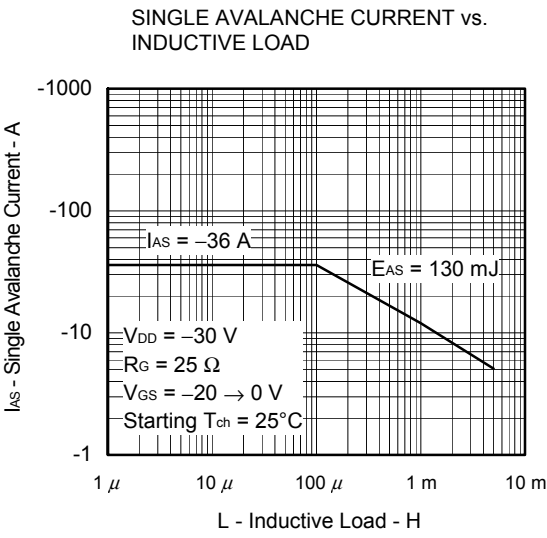


DYNAMIC INPUT/OUTPUT CHARACTERISTICS



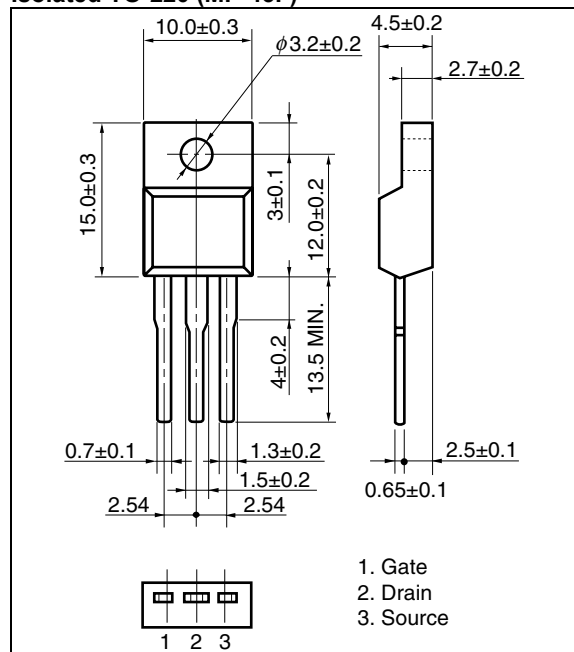
SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



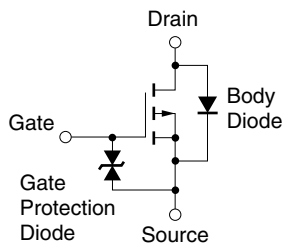


PACKAGE DRAWING (Unit: mm)

Isolated TO-220 (MP-45F)



EQUIVALENT CIRCUIT



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD.  
When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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